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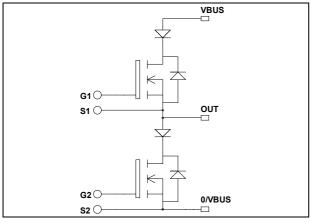






Phase leg with Series diodes MOSFET Power Module

$$\begin{split} V_{DSS} &= 1200 V \\ R_{DSon} &= 200 m \Omega \ typ \ @ \ Tj = 25^{\circ} C \\ I_D &= 50 A \ @ \ Tc = 25^{\circ} C \end{split}$$



GI VBUS O/VBUS OUT

Application

• Zero Current Switching resonant mode

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage	1200	V	
I_D	Continuous Drain Current	$T_c = 25^{\circ}C$	50	
<i>D</i>		$T_c = 80$ °C	37	Α
I_{DM}	Pulsed Drain current	200		
V_{GS}	Gate - Source Voltage	±30	V	
R _{DSon}	Drain - Source ON Resistance		240	mΩ
P_{D}	Maximum Power Dissipation	ower Dissipation $T_c = 25^{\circ}C$		W
I_{AR}	Avalanche current (repetitive and non repetitive)		12	A
E_{AR}	Repetitive Avalanche Energy		30	m I
E_{AS}	Single Pulse Avalanche Energy		1300	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1200V$ $T_j = 25^{\circ}C$			1.5	mA
		$V_{GS} = 0V, V_{DS} = 1000V$ $T_j = 125^{\circ}C$;		6	ША
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 25A$		200	240	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 6mA$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±450	nA

Dynamic Characteristics

·	Characteristic	Test Conditions	Min	Тур	Max	Unit	
C_{iss}	Input Capacitance	$V_{GS} = 0V$		15.2			
C_{oss}	Output Capacitance	$V_{DS} = 25V$		2.2		nF	
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		0.42			
Q_{g}	Total gate Charge	$V_{GS} = 10V$		600			
Q_{gs}	Gate – Source Charge	$V_{Bus} = 600V$		84		nC	
Q_{gd}	Gate – Drain Charge	$I_D = 50A$		390			
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		10			
T_{r}	Rise Time	$\begin{aligned} V_{GS} &= 15V \\ V_{Bus} &= 800V \\ I_D &= 50A \\ R_G &= 0.8\Omega \end{aligned}$		10		ns	
$T_{d(off)}$	Turn-off Delay Time			68			
T_{f}	Fall Time			36			
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		2.79		T	
E_{off}	Turn-off Switching Energy	$-V_{GS} = 15V, V_{Bus} = 800V$ $I_{D} = 50A, R_{G} = 0.8\Omega$		0.6		mJ	
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		5.6		.	
E _{off}	Turn-off Switching Energy	$\begin{array}{l} - V_{GS} = 15V, V_{Bus} = 800V \\ I_{D} = 50A, R_{G} = 0.8\Omega \end{array}$		0.81		mJ	

Series diode ratings and characteristics

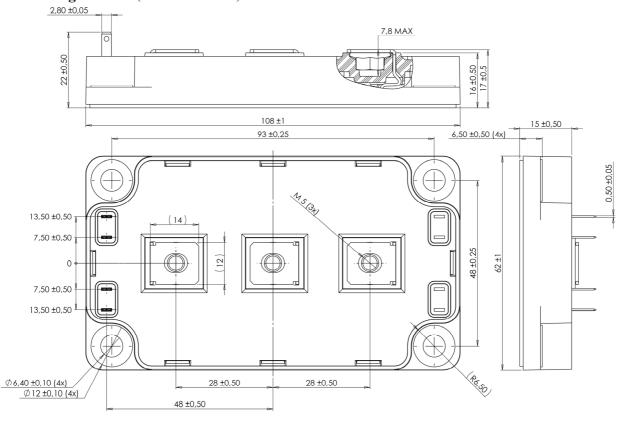
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$ $T_i = 125^{\circ}C$			250 600	μΑ
I_{F}	DC Forward Current		$T_c = 70$ °C		120		A
	Diode Forward Voltage	$I_F = 120A$		2	2.5		
$V_{\rm F}$		$I_F = 240A$		2.3		V	
		$I_F = 120A$	$T_j = 125$ °C		1.8		
t	Reverse Recovery Time		$T_j = 25$ °C		400		ns
t _{rr}		$I_F = 120A$ $V_R = 800V$	$T_{j} = 125^{\circ}C$		470		115
Q _{rr}	Reverse Recovery Charge	$di/dt = 400A/\mu s$	$T_j = 25^{\circ}C$		2.4		μC
			$T_{j} = 125^{\circ}C$		8		μ



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance		Transistor				0.1	°C/W
			Series diode				0.46	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V	
T_{J}	Operating junction temperature range			-40		150		
T_{STG}	Storage Temperature Range						125	°C
$T_{\rm C}$	Operating Case Temperature				-40		100	
Torque	Mounting forgue	To heat	sink	M6	3		5	N.m
Torque		For terr	ninals	M5	2		3.5	11.111
Wt	Package Weight						300	g

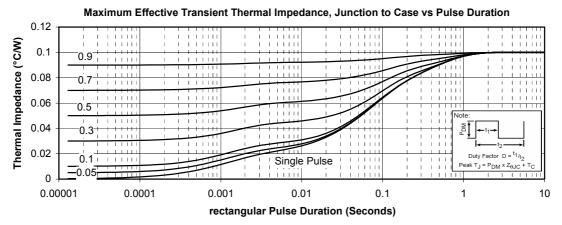
SP6 Package outline (dimensions in mm)

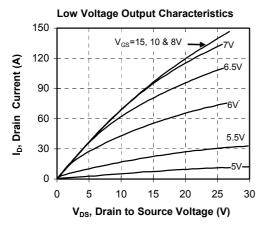


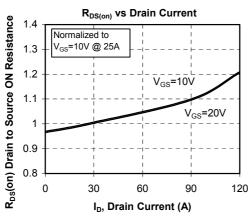
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

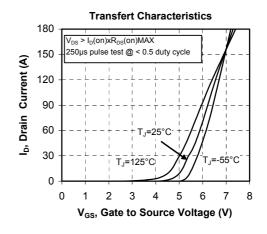


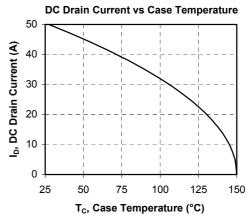
Typical Performance Curve



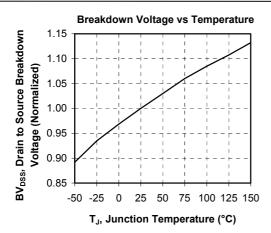


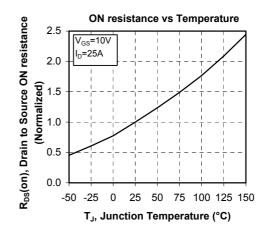


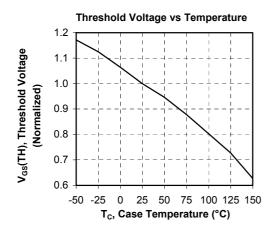


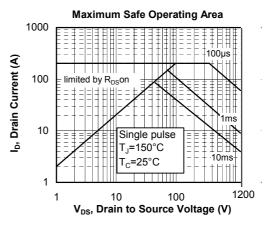


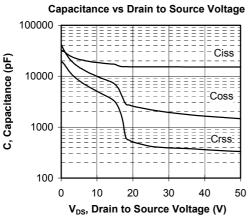


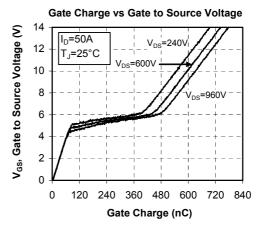




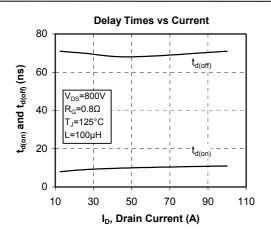


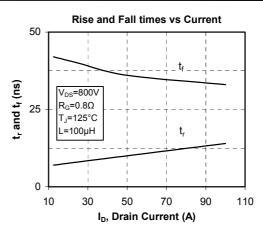


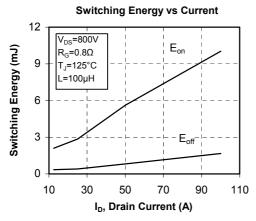


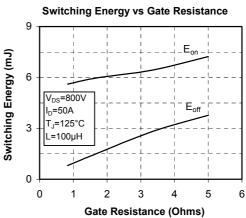


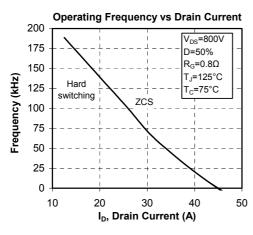


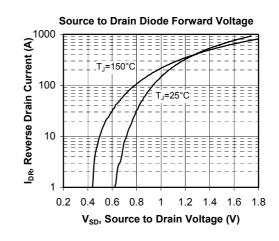














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